

**SEMICONDUCTOR DEVICES AND  
METHODS OF FORMING THE SAME**

Abstract of the Disclosure

Semiconductor devices that include a semiconductor substrate and a gate line are provided. The gate line is on the semiconductor substrate and includes a gate  
5 insulation pattern and a gate electrode which are stacked on the substrate in the order named. A spacer is on a sidewall of the gate line. A conductive line pattern is on the gate line. The conductive line pattern is parallel with the gate line and is electrically connected to the gate electrode.

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